Optical Microlithography XXIX

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## Contents

[ v ] vii Authors

[ xi ] Conference Committee

### SESSION 1: KEYNOTE SESSION

<table>
<thead>
<tr>
<th>Paper ID</th>
<th>Title</th>
<th>Notice</th>
</tr>
</thead>
<tbody>
<tr>
<td>9780 02</td>
<td>Patterning challenges in the sub-10 nm era (Keynote Paper) [9780-1]</td>
<td></td>
</tr>
</tbody>
</table>

### SESSION 2: PUSHING OPTICAL LIMIT

<table>
<thead>
<tr>
<th>Paper ID</th>
<th>Title</th>
<th>Notice</th>
</tr>
</thead>
<tbody>
<tr>
<td>9780 04</td>
<td>Expected innovations of optical lithography in the next 10 years (Invited Paper) [9780-3]</td>
<td></td>
</tr>
<tr>
<td>9780 05</td>
<td>Computational process modeling and correction in a multi-patterning era (Invited Paper) [9780-4]</td>
<td></td>
</tr>
<tr>
<td>9780 06</td>
<td>Lithographic qualification of high-transmission mask blank for 10nm node and beyond [9780-5]</td>
<td></td>
</tr>
<tr>
<td>9780 07</td>
<td>Ultimate intra-wafer critical dimension uniformity control by using lithography and etch tool corrections [9780-6]</td>
<td></td>
</tr>
</tbody>
</table>

### SESSION 3: IMAGE AND PROCESS CONTROL

<table>
<thead>
<tr>
<th>Paper ID</th>
<th>Title</th>
<th>Notice</th>
</tr>
</thead>
<tbody>
<tr>
<td>9780 08</td>
<td>Lower BW and its impact on the patterning performance [9780-7]</td>
<td></td>
</tr>
<tr>
<td>9780 09</td>
<td>Intra-lot wafer by wafer overlay control using integrated and standalone metrology combined sampling [9780-8]</td>
<td></td>
</tr>
<tr>
<td>9780 0A</td>
<td>Reduction of wafer-edge overlay errors using advanced correction models, optimized for minimal metrology requirements [9780-9]</td>
<td></td>
</tr>
<tr>
<td>9780 0B</td>
<td>Overcoming low-alignment signal contrast induced alignment failure by alignment signal enhancement [9780-10]</td>
<td></td>
</tr>
<tr>
<td>9780 0C</td>
<td>Lithographic imaging-driven pattern edge placement errors at 10nm node [9780-11]</td>
<td></td>
</tr>
</tbody>
</table>

### SESSION 4: NEGATIVE TONE MATERIALS AND PROCESSES: JOINT SESSION WITH CONFERENCE 9779 AND 9780

<table>
<thead>
<tr>
<th>Paper ID</th>
<th>Title</th>
<th>Notice</th>
</tr>
</thead>
<tbody>
<tr>
<td>9780 0D</td>
<td>Process window variation comparison between NTD and PTD for various contact type [9780-12]</td>
<td></td>
</tr>
<tr>
<td>9780 0E</td>
<td>Ultimate 2D resolution printing with negative tone development [9780-13]</td>
<td></td>
</tr>
</tbody>
</table>
### SESSION 5  COMPUTATIONAL LITHOGRAPHY

| 9780 0H | Machine learning (ML)-guided OPC using basis functions of polar Fourier transform [9780-16] |
| 9780 0I | Bayesian inference for OPC modeling [9780-17] |
| 9780 0J | OPC recipe optimization using genetic algorithm [9780-18] |
| 9780 0K | Impact of bandwidth variation on OPC model accuracy [9780-19] |

### SESSION 6  MATERIAL AND PROCESS DRIVEN RESOLUTION ENHANCEMENTS

| 9780 0M | An integrated source/mask/DSA optimization approach [9780-21] |
| 9780 0N | Multi-layer VEB model: capturing interlayer etch process effects for self-aligned via in multi-patterning process scheme [9780-22] |
| 9780 0O | Mask defect printability in the Self-Aligned Quadruple Patterning (SAQP) process [9780-23] |

### SESSION 7  DESIGN AND LITHO OPTIMIZATION: JOINT SESSION WITH CONFERENCES 9780 AND 9781

| 9780 0P | Standard cell pin access and physical design in advanced lithography (Invited Paper) [9780-24] |
| 9780 0Q | Incorporating photomask shape uncertainty in computational lithography [9780-25] |

### SESSION 8  NON-IC APPLICATIONS

| 9780 0R | Alternative high-resolution lithographic technologies for optical applications (Invited Paper) [9780-26] |
| 9780 0T | High dynamic grayscale lithography with an LED-based micro-image stepper [9780-28] |
| 9780 0U | Firefly: an optical lithographic system for the fabrication of holographic security labels [9780-29] |
| 9780 0V | Phase analysis of amplitude binary mask structures [9780-30] |

### SESSION 9  OVERLAY OPTIMIZATION: JOINT SESSION WITH CONFERENCES 9778 AND 9780

| 9780 0W | Patterned wafer geometry (PWG) metrology for improving process-induced overlay and focus problems (Invited Paper) [9780-31] |
| 9780 0X | Improvement of unbalanced illumination induced telecentricity within the exposure slit [9780-32] |
### SESSION 10 TOOLINGS

<table>
<thead>
<tr>
<th>9780 0Y</th>
<th>High-order aberration control during exposure for leading-edge lithography projection optics [9780-33]</th>
</tr>
</thead>
<tbody>
<tr>
<td>9780 10</td>
<td>The ArF laser for the next-generation multiple-patterning immersion lithography supporting green operations [9780-35]</td>
</tr>
<tr>
<td>9780 11</td>
<td>NXT:1980Di immersion scanner for 7nm and 5nm production nodes [9780-36]</td>
</tr>
<tr>
<td>9780 12</td>
<td>Next-generation immersion scanner optimizing on-product performance for 7nm node [9780-37]</td>
</tr>
<tr>
<td>9780 13</td>
<td>Investigation of systematic CD distribution error on intrafield [9780-50]</td>
</tr>
</tbody>
</table>

### INTERACTIVE POSTER SESSION

| 9780 14 | Periodic sub-100nm structures fabricated by proximity i-line mask-aligner lithography (and self-aligned double patterning) [9780-38] |
| 9780 15 | Innovative method to suppress local geometry distortions for fabrication of interdigitated electrode arrays with nano gaps [9780-39] |
| 9780 16 | Coherence management in lithography printing systems [9780-40] |
| 9780 17 | Fabricate large area and defect free periodic structures with advance achromatic laser interference lithography [9780-41] |
| 9780 18 | Optimizing the lithography model calibration algorithms for NTD process [9780-42] |
| 9780 19 | Source mask optimization using 3D mask and compact resist models [9780-43] |
| 9780 1A | Layer aware source mask target optimization [9780-44] |
| 9780 1C | A novel full chip process window OPC based on matrix retargeting [9780-46] |
| 9780 1E | Simple method for decreasing wafer topography effect for implant mask [9780-48] |
| 9780 1F | Native conflict awared layout decomposition in triple patterning lithography using bin-based library matching method [9780-49] |
| 9780 1G | Means to improve light source productivity: from proof of concept to field implementation [9780-51] |
| 9780 1H | Neon reduction program on Cymer ArF light sources [9780-52] |
| 9780 1I | The next-generation ArF excimer laser for multiple-patterning immersion lithography with helium free operation [9780-54] |
9780 1J Rare resource supply crisis and solution technology for semiconductor manufacturing [9780-55]
9780 1K Progress on glass ceramic ZERODUR enabling nanometer precision [9780-57]
9780 1L Spatial conversion of excimer laser beam [9780-56]
9780 1M Optimal design of wide-view-angle waveplate used for polarimetric diagnosis of lithography system [9780-58]
9780 1N Confocal position alignment in high-precision wavefront error metrology using Shack-Hartmann wavefront sensor [9780-59]
9780 1O SEM signal emulation for 2D patterns [9780-60]
9780 1P Source mask optimization study based on latest Nikon immersion scanner [9780-61]
9780 1Q CDU budget breakdown as a diagnostic method for imaging sensitivity in HVM [9780-62]
9780 1R Inverse polarizer on immersion lithography mask [9780-63]
9780 1S Line edge roughness frequency analysis for SAQP process [9780-64]
9780 1T Fabrication of dual-wavelength diffractive beam splitters using maskless optical lithography based on a digital micromirror device [9780-65]
9780 1U OPC for curved designs in application to photonics on silicon [9780-66]
9780 1V Pixel-based mask optimization via particle swarm optimization algorithm for inverse lithography [9780-67]
Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Aarts, Igor, 0B
Adam, Kostas, 19
Agudelo, Viviana, 0U
Alagna, Paolo, 08, 0K
Amako, Jun, 1T
Amézquita, Ricardo, 0U
Amézquita, Sebastián, 0U
Anunciado, Roy, 1Q
Arnold, John, 06
Asthana, Abhishek, 0J
Bailey, Todd, 06, 0N
Bar, Yuval, 0N
Barkelid, Maria, 1Q
Basilman, Jan, 08
Baylé, Sébastien, 1U
Bernai, André, 0U
Bernasconi, Johana, 16
Bleiman, Ben, 06
Böcker, Paul, 0A
Bolton, John, 06
Bouman, Wim, 0X
Bourgin, Yannick, 0R, 14
Bramati, Arianna, 0V, 16
Bräuer, Andreas, 0T
Braylovska, Mariya, 1Q
Brunner, Timothy A., 0W
Burbin, Andrew, 01
Burkhardt, Martin, 0E
Burns, Sean, 06
Byun, Jin-Moo, 0A
Cacouris, Ted, 1G, 1H
Calderón, Jorge, 0U
Chahine, Charlotte, 07
Chang, Chansam, 0X
Chen, Ao, 19, 1A
Chen, Chun-Kuang, 1R
Chen, K. C., 18
Chen, Lijun, 06
Chen, Minfeng, 1R
Chen, Xiuguo, 1M
Chen, Yulu, 1S
Choi, Suhuyeong, 0H
Choi, Young Sin, 09
Chou, Shuo-Yen, 1R
Chung, Angeline, 19
Cline, Brian, 0P
Colburn, Matthew, 06
Conley, Will, 08, 0K, 1G
Cremer, Sébastien, 1U
de Boeij, Wim P., 0B, 0X, 11
de Graaf, Roelof, 08, 0X, 11
Dirrenberger, Mathieu, 1U
Dixit, Girish, 07
Droste, Richard, 0B, 0X, 11
Dusa, Mircea, 07
Eckstein, Hans-Christoph, 0T
El-Sewefy, Omar, 19, 1P
Enami, Tatsuo, 1J
Erdmann, Andreas, 0M, 0Q
Farys, Vincent, 1U
Faure, Tom, 06
Felix, Nelson, 06
Fischer, Dan, 06
Foong, Yee Mei, 19, 1A
Fryer, David, 0I
Fu, Chien-Chung, 17
Fühner, Tim, 0M
Fujimoto, Issei, 12
Fukuda, Hitomi, 1J
Furubayashi, Ken, 0O
Gao, Gen-Sheng, 1P
Gao, Weimin, 1O
Gau, Tsai-Sheng, 1R
Ge, Adam, 1S
Gomez, Juan-Manuel, 1Q
Graur, Ioana, 06
Grishkanich, Alexander, 1L
Gu, Honggang, 1M
Guerrero, James, 1A
Hanson, Justin K., 1Q
Hasegawa, Keisuke, 0Y
Hayakawa, Akira, 12
Hellin, David, 07
Herzig, Hans Peter, 0V, 16
Hirayama, Toru, 0Y, 12
Hirayanagi, Noriyuki, 04
Hong, Le, 1C
Hsu, Stephen, 0K, 1A
Hu, C. M., 18
Hu, Lin, 06, 0N
Hu, Sophia, 1J
Hwang, Hyunwoo, 0B
Iida, Kazunori, 0O
Ikezawa, Hironori, 0Y
Inoue, Daisuke, 0Y
Ishida, Keisuke, 10
Ishiyama, Satoshi, 0Y, 12
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Opening Remarks
Andreas Erdmann, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie IISB (Germany)
Jongwook Kye, GLOBALFOUNDRIES Inc. (United States)

1 Keynote Session
Andreas Erdmann, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie IISB (Germany)
Jongwook Kye, GLOBALFOUNDRIES Inc. (United States)

2 Pushing Optical Limit
Kafai Lai, IBM Thomas J. Watson Research Center (United States)
Geert Vandenberghe, IMEC (Belgium)

3 Image and Process Control
Yuri Granik, Mentor Graphics Corporation (United States)
Kazuhiro Takahashi, Canon Inc. (Japan)

4 Negative Tone Materials and Processes: Joint Session with Conferences 9779 and 9780
Sean D. Burns, IBM Corporation (United States)
Carlos Fonseca, Tokyo Electron America, Inc. (United States)

5 Computational Lithography
Soichi Owa, Nikon Corporation (Japan)
John S. Petersen, Petersen Advanced Lithography, Inc. (United States)

6 Material and Process Driven Resolution Enhancements
Will E. Conley, Cymer LLC (United States)
Harsha Grunes, Intel Corporation (United States)

7 Design and Litho Optimization: Joint Session with Conferences 9780 and 9781
Daniel Sarlette, Infineon Technologies Dresden (Germany)

8 Non-IC Applications
Sachiko Kobayashi, Toshiba Corporation (Japan)
Reinhard Völkel, SUSS MicroOptics SA (Switzerland)

9 Overlay Optimization: Joint Session with Conferences 9778 and 9780
John C. Robinson, KLA-Tencor Corporation (United States)
Young Seog Kang, SAMSUNG Electronics Company, Ltd. (Korea, Republic of)
Toolings

Tsai-Sheng Gau, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)
Bernd Geh, Carl Zeiss SMT Inc. (United States)

Concluding Remarks

Andreas Erdmann, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie IISB (Germany)
Jongwook Kye, GLOBALFOUNDRIES Inc. (United States)